

MITSUBISHI LSIs M5K4164ANP-20

65536-BIT (65536-WORD BY 1-BIT) DYNAMIC RAM

DESCRIPTION

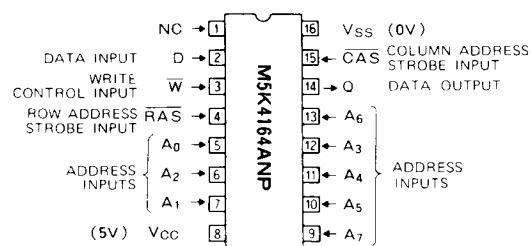
This is a family of 65536-word by 1-bit dynamic RAMs, fabricated with the high performance N-channel silicon-gate MOS process, and is ideal for large-capacity memory systems where high speed, low power dissipation, and low costs are essential. The use of double-layer polysilicon process technology and a single-transistor dynamic storage cell provide high circuit density at reduced costs, and the use of dynamic circuitry including sense amplifiers assures low power dissipation. Multiplexed address inputs permit both a reduction in pins to the standard 16-pin package configuration and an increase in system densities. The M5K4164ANP operates on a 5V power supply using the on-chip substrate bias generator.

FEATURES

Type name	Access time (max) (ns)	Cycle time (min) (ns)	Power dissipation (typ) (mW)
M5K4164ANP-20	200	330	125

- Single 5V±20/ supply
- Low standby power dissipation: 22.0 mW (max)
- Low operating power dissipation: 225 mW (max)
- Unlatched output enables two-dimensional chip selection and extended page boundary
- Early-write operation gives common I/O capability
- Read-modify-write, RAS-only refresh, and page-mode capabilities
- All input terminals have low input capacitance and are directly TTL-compatible
- Output is three-stage and directly TTL-compatible
- 128 refresh cycles every 2ms
- (16K dynamic RAMs M5K4116P, S compatible)

PIN CONFIGURATION (TOP VIEW)



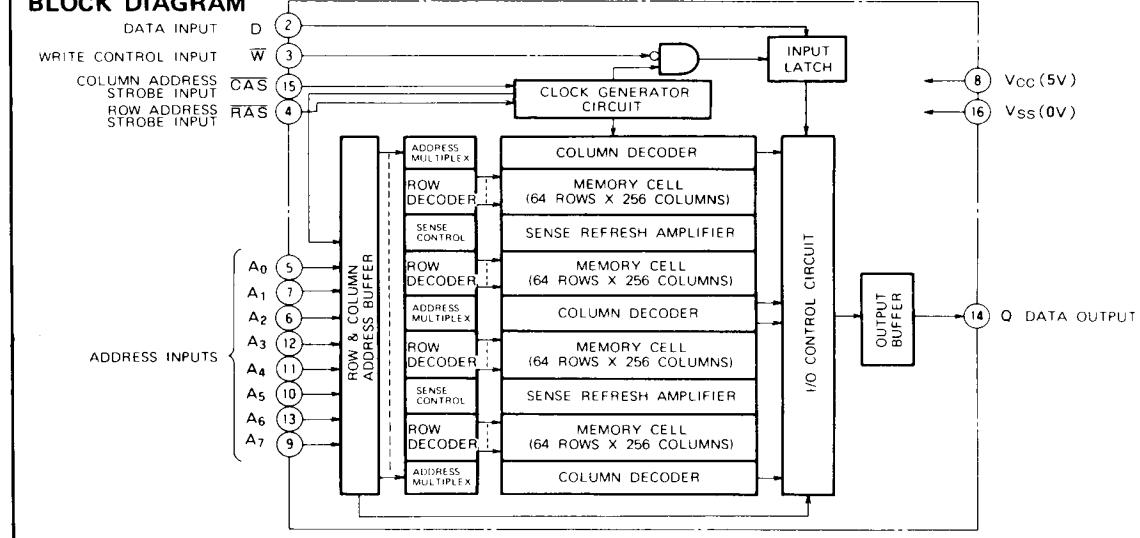
Outline 16P4

- CAS controlled output allows hidden refresh.
- Output data can be held infinitely by CAS.
- Interchangeable with Intel's 2164 and Motorola's MCM 6665 in pin configuration.

APPLICATION

- Main memory unit for computers.

BLOCK DIAGRAM



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ELECTRIC

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FUNCTION

The M5K4164ANP provides, in addition to normal read, write, and read-modify-write operations, a number of other functions, e.g., page mode, RAS-only refresh, and delayed-write. The input conditions for each are shown in Table 1.

Table 1 Input conditions for each mode

Operation	Inputs							Output	Refresh	Remarks
	RAS	CAS	W	D	Row address	Column address	Q			
Read	ACT	ACT	NAC	DNC	APD	APD	VLD	YES	YES	Page mode
Write	ACT	ACT	ACT	VLD	APD	APD	OPN	YES	YES	identical except refresh is NO
Read-modify-write	ACT	ACT	ACT	VLD	APD	APD	VLD	YES	YES	
RAS only refresh	ACT	NAC	DNC	DNC	APD	DNC	OPN	YES	YES	
Hidden refresh	ACT	ACT	DNC	DNC	APD	DNC	VLD	YES	YES	
Standby	NAC	DNC	DNC	DNC	DNC	DNC	OPN	NO	NO	

Note ACT: active, NAC: nonactive, DNC: don't care, VLD: valid, APD: applied, OPN: open

SUMMARY OF OPERATIONS

Addressing

To select one of the 65536 memory cells in the M5K4164ANP the 16-bit address signal must be multiplexed into 8 address signals, which are then latched into the on-chip latch by two externally-applied clock pulses. First, the negative-going edge of the row-address-strobe pulse (RAS) latches the 8 row-address bits; next, the negative-going edge of the column-address-strobe pulse (CAS) latches the 8 column-address bits. Timing of the RAS and CAS clocks can be selected by either of the following two methods:

1. The delay time from RAS to CAS $t_{d(RAS-CAS)}$ is set between the minimum and maximum values of the limits. In this case, the internal CAS control signals are inhibited almost until $t_{d(RAS-CAS) \max}$ ('gated CAS operation). The external CAS signal can be applied with a margin not affecting the on-chip circuit operations, e.g. access time, and the address inputs can be easily changed from row address to column address.
2. The delay time $t_{d(RAS-CAS)}$ is set larger than the maximum value of the limits. In this case the internal inhibition of CAS has already been released, so that the internal CAS control signals are controlled by the externally applied CAS, which also controls the access time.

Data Input

Data to be written into a selected cell is strobed by the later of the two negative transitions of W input and CAS input. Thus when the W input makes its negative transition prior to CAS input (early write), the data input is strobed by CAS, and the negative transition of CAS is set as the

reference point for set-up and hold times. In the read-write or read-modify-write cycles, however, when the W input makes its negative transition after CAS, the W negative transition is set as the reference point for setup and hold times.

Data Output Control

The output of the M5K4164ANP is in the high-impedance state when CAS is high. When the memory cycle in progress is a read, read-modify-write, or a delayed-write cycle, the data output will go from the high-impedance state to the active condition, and the data in the selected cell will be read. This data output will have the same polarity as the input data. Once the output has entered the active condition, this condition will be maintained until CAS goes high, irrespective of the condition of RAS.

The output will remain in the high-impedance state throughout the entire cycle in an early-write cycle.

These output conditions, of the M5K4164ANP which can readily be changed by controlling the timing of the write pulse in a write cycle, and the width of the CAS pulse in a read cycle, offer capabilities for a number of applications, as follows.

1. Common I/O Operation

If all write operations are performed in the early-write mode, input and output can be connected directly to give a common I/O data bus.

2. Data Output Hold

The data output can be held between read cycles, without lengthening the cycle time. This enables extremely flexible clock-timing settings for RAS and CAS.

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3. Two Methods of Chip Selection

Since the output is not latched, CAS is not required to keep the outputs of selected chips in the matrix in a high-impedance state. This means that CAS and/or RAS can both be decoded for chip selection.

4. Extended-Page Boundary

By decoding CAS, the page boundary can be extended beyond the 256 column locations in a single chip. In this case, RAS must be applied to all devices.

Page-Mode Operation

This operation allows for multiple-column addressing at the same row address, and eliminates the power dissipation associated with the negative-going edge of RAS, because once the row address has been strobed, RAS is maintained. Also, the time required to strobe in the row address for the second and subsequent cycles is eliminated, thereby decreasing the access and cycle times.

Refresh

Each of the 128 rows ($A_0 \sim A_6$) of the M5K4164ANP must be refreshed every 2 ms to maintain data. The methods of refreshing for the M5K4164ANP are as follows.

1. Normal Refresh

Read cycle and Write cycle (early write, delayed write or read-modify-write) refresh the selected row as defined by the low order (RAS) addresses. Any write cycle, of course, may change the state of the selected cell. Using a read, write, or read-modify-write cycle for refresh is not recommended for systems which utilize "write-OR" outputs since output bus contention will occur.

2. RAS Only Refresh

A RAS-only refresh cycle is the recommended technique for most applications to provide for data retention. A RAS-only refresh cycle maintains the output in the high-impedance state with a typical power reduction of 20% over a read or write cycle.

3. Hidden Refresh

A feature of the M5K4164ANP is that refresh cycles may be performed while maintaining valid data at the output pin by extending the CAS active time from a previous memory read cycle. This feature is referred to as hidden refresh.

Hidden refresh is performed by holding CAS at V_{IL} and taking RAS high and after a specified precharge period, executing a RAS-only cycling, but with CAS held low.

The advantage of this refresh mode is that data can be held valid at the output data port indefinitely by leaving the CAS asserted. In many applications this eliminates the need for off-chip latches.

Power Dissipation

Most of the circuitry in the M5K4164ANP is dynamic, and most of the power is dissipated when addresses are strobed. Both RAS and CAS are decoded and applied to the M5K4164ANP as chip-select in the memory system, but if RAS is decoded, all unselected devices go into stand-by independent of the CAS condition, minimizing system power dissipation.

Power Supplies

The M5K4164ANP operates on a single 5V power supply.

A wait of some 500 μ s and eight or more dummy cycles is necessary after power is applied to the device before memory operation is achieved.

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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Limits	Unit
V_{CC}	Supply voltage		-1 ~ 7	V
V_I	Input voltage	With respect to V_{SS}	-1 ~ 7	V
V_O	Output voltage		-1 ~ 7	V
I_O	Output current		50	mA
P_d	Power dissipation	$T_a = 25^\circ C$	700	mW
T_{opr}	Operating free-air temperature range		0 ~ 70	°C
T_{stg}	Storage temperature range		-65 ~ 150	°C

RECOMMENDED OPERATING CONDITIONS ($T_a = 0 \sim 70^\circ C$, unless otherwise noted) (Note 1)

Symbol	Parameter	Limits			Unit
		Min	Nom	Max	
V_{CC}	Supply voltage	4.5	5	5.5	V
V_{SS}	Supply voltage	0	0	0	V
V_{IH}	High-level input voltage, all inputs	2.4		$V_{CC} + 1$	V
V_{IL}	Low-level input voltage, all inputs	-2		0.8	V

Note 1 All voltage values are with respect to V_{SS}

ELECTRICAL CHARACTERISTICS ($T_a = 0 \sim 70^\circ C$, $V_{CC} = 5V \pm 10\%$, $V_{SS} = 0V$, unless otherwise noted) (Note 2)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V_{OH}	High-level output voltage	$I_{OH} = -5mA$	2.4			V_{CC} V
V_{OL}	Low-level output voltage	$I_{OL} = 4.2mA$		0	0.4	V
I_{OZ}	Off-state output current	Q floating $0V \leq V_{OUT} \leq 5.5V$	-10		10	μA
I_I	Input current	$0V \leq V_{IN} \leq 6.5V$, All other pins = 0V	-10		10	μA
$I_{CC1(AV)}$	Average supply current from V_{CC} , operating (Note 3, 4)	$M5K4164ANP-20$ RAS , CAS cycling $t_{CR} = t_{CW} = \text{min. output open}$			40	mA
I_{CC2}	Supply current from V_{CC} , standby	$RAS = V_{IH}$ output open			4	mA
$I_{CC3(AV)}$	Average supply current from V_{CC} , refreshing (Note 3)	$M5K4164ANP-20$ RAS cycling $CAS = V_{IH}$ $t_{C(REF)} = \text{min. output open}$			30	mA
$I_{CC4(AV)}$	Average supply current from V_{CC} , page mode (Note 3, 4)	$M5K4164ANP-20$ $RAS = V_{IL}$, CAS cycling $t_{CPG} = \text{min. output open}$			30	mA
$C_I(A)$	Input capacitance, address inputs				5	pF
$C_I(D)$	Input capacitance, data input	$V_I = V_{SS}$			5	pF
$C_I(W)$	Input capacitance, write control input	$f = 1MHz$			7	pF
$C_I(RAS)$	Input capacitance, RAS input	$V_I = 25mVrms$			10	pF
$C_I(CAS)$	Input capacitance, CAS input				10	pF
C_O	Output capacitance	$V_O = V_{SS}$, $f = 1MHz$, $V_I = 25mVrms$			7	pF

Note 2 Current flowing into an IC is positive, out is negative.

3 $I_{CC1(AV)}$, $I_{CC3(AV)}$, and $I_{CC4(AV)}$ are dependent on cycle rate. Maximum current is measured at the fastest cycle rate.

4 $I_{CC1(AV)}$ and $I_{CC4(AV)}$ are dependent on output loading. Specified values are obtained with the output open.

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TIMING REQUIREMENTS (For Read, Write, Read-Modify-Write, Refresh, and Page-Mode Cycle)

($T_a = 0 \sim 70^\circ C$, $V_{CC} = 5V \pm 10\%$, $V_{SS} = 0V$, unless otherwise noted, See notes 5, 6 and 7)

Symbol	Parameter	Alternative Symbol	M5K4164ANP-20		Unit	
			Limits			
			Min	Max		
t_{CRF}	Refresh cycle time	t_{REF}		2	ns	
$t_{W(RASH)}$	RAS high pulse width	t_{RP}	120		ns	
$t_{W(RASL)}$	RAS low pulse width	t_{RAS}	200	10000	ns	
$t_{W(CASL)}$	CAS low pulse width	t_{CAS}	100	∞	ns	
$t_{W(CASH)}$	CAS high pulse width	(Note 8)	t_{CPN}	40	ns	
$t_h(RAS-CAS)$	CAS hold time after RAS		t_{CSH}	200	ns	
$t_h(CAS-RAS)$	RAS hold time after CAS		t_{RSH}	100	ns	
$t_d(CAS-RAS)$	Delay time, CAS to RAS	(Note 9)	t_{CRP}	-20	ns	
$t_d(RAS-CAS)$	Delay time, RAS to CAS	(Note 10)	t_{RCD}	30	100	ns
$t_{SU(RA-RAS)}$	Row address setup time before RAS		t_{ASR}	0	ns	
$t_{SU(CA-CAS)}$	Column address setup time before CAS		t_{ASC}	0	ns	
$t_h(RAS-RA)$	Row address hold time after RAS		t_{RAH}	25	ns	
$t_h(CAS-CA)$	Column address hold time after CAS		t_{CAH}	35	ns	
$t_h(RAS-CA)$	Column address hold time after RAS		t_{CAR}	120	ns	
t_{TLH}	Transition time	t_T		3	50	ns
t_{TLH}						

Note 5: An initial pause of 500 μ s is required after power up followed by any eight RAS or RAS/CAS cycles before proper device operation is achieved.

6: The switching characteristics are defined as $t_{TLH} = t_{T_{LH}} = 5$ ns.

7: Reference levels of input signals are $V_{IH\ min}$ and $V_{IL\ max}$. Reference levels for transition time are also between V_{IH} and V_{IL} .

8: Except for page mode.

9: $t_{d(CAS\ RAS)}$ requirement is only applicable for RAS/CAS cycles preceded by a CAS only cycle (i.e., For systems where CAS has not been decoded with RAS)

10: Operation within the $t_d(RAS-CAS)$ max limit insures that $t_a(RAS)$ max can be met. $t_d(RAS-CAS)$ max is specified reference point only, if

$t_d(RAS-CAS)$ is greater than the specified $t_d(RAS-CAS)$ max limit, then access time is controlled exclusively by $t_a(CAS)$.

$t_d(RAS-CAS)$ min = $t_h(RAS-RA)$ min + 2 t_{TLH} ($t_{T_{LH}}$) + $t_{SU(CA-CAS)}$ min.

SWITCHING CHARACTERISTICS (Ta = 0 ~ 70°C, VCC = 5V ± 10%, VSS = 0V, unless otherwise noted)

Read Cycle

Symbol	Parameter	Alternative Symbol	M5K4164ANP-20		Unit	
			Limits			
			Min	Max		
t_{CR}	Read cycle time	t_{RC}	330		ns	
$t_{SU(R-CAS)}$	Read setup time before CAS	t_{RCS}	0		ns	
$t_h(CAS-R)$	Read hold time after CAS	(Note 11)	t_{RCH}	0	ns	
$t_h(RAS-R)$	Read hold time after RAS	(Note 11)	t_{RRH}	25	ns	
$t_{DIS(CAS)}$	Output disable time	(Note 12)	t_{OFF}	0	50	ns
$t_a(CAS)$	CAS access time	(Note 13)	t_{CAC}		100	ns
$t_a(RAS)$	RAS access time	(Note 14)	t_{RAC}		200	ns

Note 11: Either $t_h(RAS-R)$ or $t_h(CAS-R)$ must be satisfied for a read cycle.

Note 12: $t_{DIS(CAS)}$ max defines the time at which the output achieves the open circuit condition and is not reference to V_{OH} or V_{OL} .

Note 13: This is the value when $t_d(RAS-CAS) \geq t_d(RAS-CAS)$ max. Test conditions: Load = 2T TL, $C_L = 100pF$

Note 14: This is the value when $t_d(RAS-CAS) < t_d(RAS-CAS)$ max. When $t_d(RAS-CAS) \geq t_d(RAS-CAS)$ max, $t_a(RAS)$ will increase by the amount that $t_d(RAS-CAS)$ exceeds the value shown. Test conditions, Load = 2T TL, $C_L = 100pF$

Write Cycle

Symbol	Parameter	Alternative Symbol	M5K4164ANP-20		Unit	
			Limits			
			Min	Max		
t_{CW}	Write cycle time	t_{RC}	330		ns	
$t_{SU(W-CAS)}$	Write setup time before CAS	(Note 17)	t_{WCS}	-10	ns	
$t_h(CAS-W)$	Write hold time after CAS		t_{WCH}	55	ns	
$t_h(RAS-W)$	Write hold time after RAS		t_{WCR}	120	ns	
$t_h(W-RAS)$	RAS hold time after write		t_{RWL}	55	ns	
$t_h(W-CAS)$	CAS hold time after write		t_{CWL}	55	ns	
$t_w(W)$	Write pulse width		t_{WP}	55	ns	
$t_{SU(D-CAS)}$	Data-in setup time before CAS		t_{DS}	0	ns	
$t_h(CAS-D)$	Data in hold time after CAS		t_{DH}	55	ns	
$t_h(RAS-D)$	Data in hold time after RAS		t_{DHR}	120	ns	

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Read-Write and Read-Modify-Write Cycles

Symbol	Parameter	Alternative Symbol	M5K4164ANP-20		Unit	
			Limits			
			Min	Max		
t_{CRW}	Read-write cycle time	(Note 15)	t_{RWC}	340	ns	
t_{CRMW}	Read-modify-write cycle time	(Note 16)	t_{RMWC}	390	ns	
$t_h(w\text{-RAS})$	RAS hold time after write		t_{RWL}	55	ns	
$t_h(w\text{-CAS})$	CAS hold time after write		t_{CWL}	55	ns	
$t_w(w)$	Write pulse width		t_{WP}	55	ns	
$t_{SU}(R\text{-CAS})$	Read setup time before CAS		t_{RCS}	0	ns	
$t_d(RAS\text{-W})$	Delay time, RAS to write	(Note 17)	t_{RWD}	150	ns	
$t_d(CAS\text{-W})$	Delay time, CAS to write	(Note 17)	t_{CWD}	80	ns	
$t_{SU}(D\text{-W})$	Data-in setup time before write		t_{DS}	0	ns	
$t_h(w\text{-D})$	Data-in hold time after write		t_{DH}	55	ns	
$t_{DIS}(\text{CAS})$	Output disable time		t_{OFF}	0	50	ns
$t_a(\text{CAS})$	CAS access time	(Note 13)	t_{CAC}		100	ns
$t_a(\text{RAS})$	RAS access time	(Note 14)	t_{RAC}		200	ns

Note 15: $t_{CRW\text{min}}$ is defined as $t_{CRW\text{min}} = t_d(RAS\text{-W}) + t_h(w\text{-RAS}) + t_w(RAS\text{H}) + 3t_{TLH}(t_{THL})$

16: $t_{CRMW\text{min}}$ is defined as $t_{CRMW\text{min}} = t_a(RAS)\text{max} + t_h(w\text{-RAS}) + t_w(RAS\text{H}) + 3t_{TLH}(t_{THL})$

17: $t_{SU}(w\text{-CAS})$, $t_d(RAS\text{-W})$, and $t_d(CAS\text{-W})$ do not define the limits of operation, but are included as electrical characteristics only.

When $t_{SU}(w\text{-CAS}) \geq t_{SU}(w\text{-CAS})\text{min}$, an early-write cycle is performed, and the data output keeps the high-impedance state.

When $t_d(RAS\text{-W}) \geq t_d(RAS\text{-W})\text{min}$ and $t_d(CAS\text{-W}) \geq t_{SU}(w\text{-CAS})\text{min}$ a read-write cycle is performed, and the data of the selected address will be read out on the data output.

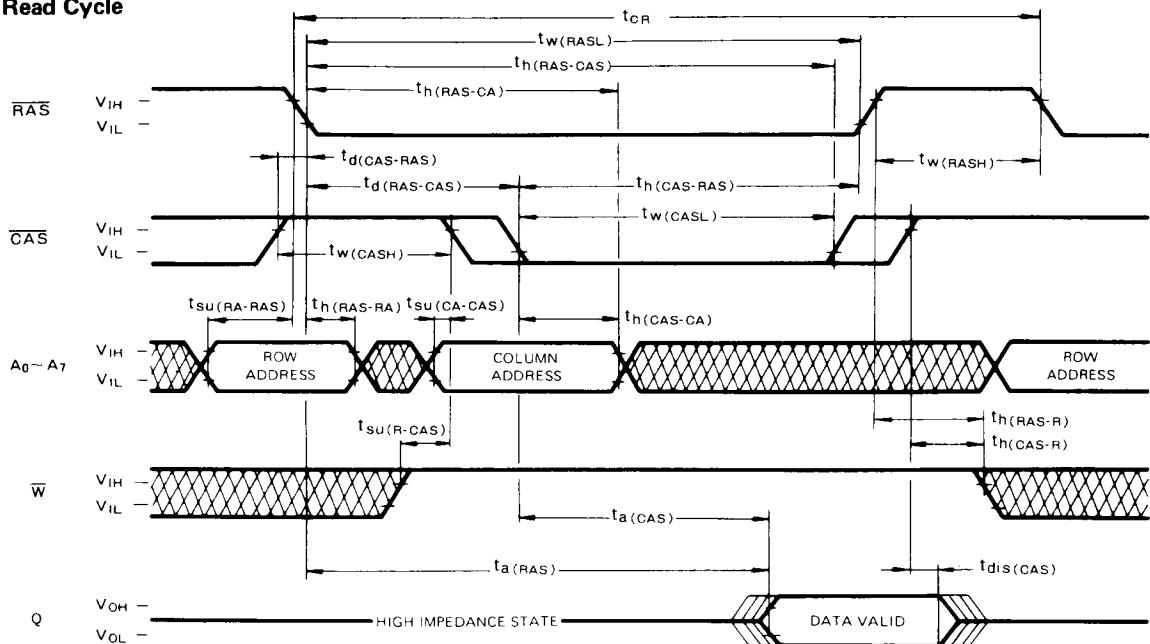
For all conditions other than those described above, the condition of data output (at access time and until CAS goes back to V_{IH}) is not defined.

Page-Mode Cycle

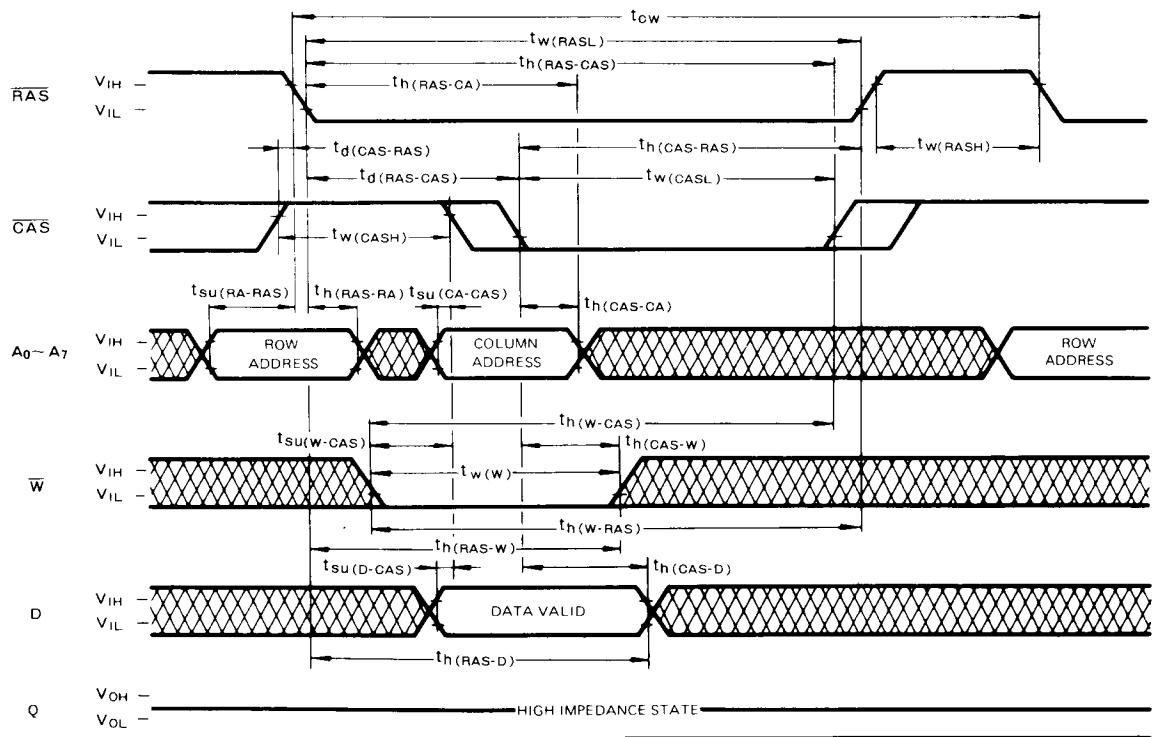
Symbol	Parameter	Alternative Symbol	M5K4164ANP-20		Unit	
			Limits			
			Min	Max		
t_{CPGR}	Page-mode read cycle time	t_{PC}	190		ns	
t_{CPGW}	Page-Mode write cycle time	t_{PC}	190		ns	
t_{CPGRW}	Page-Mode read-write cycle time	—	230		ns	
t_{CPGRMW}	Page-Mode read-modify-write cycle time	—	245		ns	
$t_w(CAS\text{H})$	CAS high pulse width	t_{CP}	80		ns	

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TIMING DIAGRAMS (Note 18)
Read Cycle

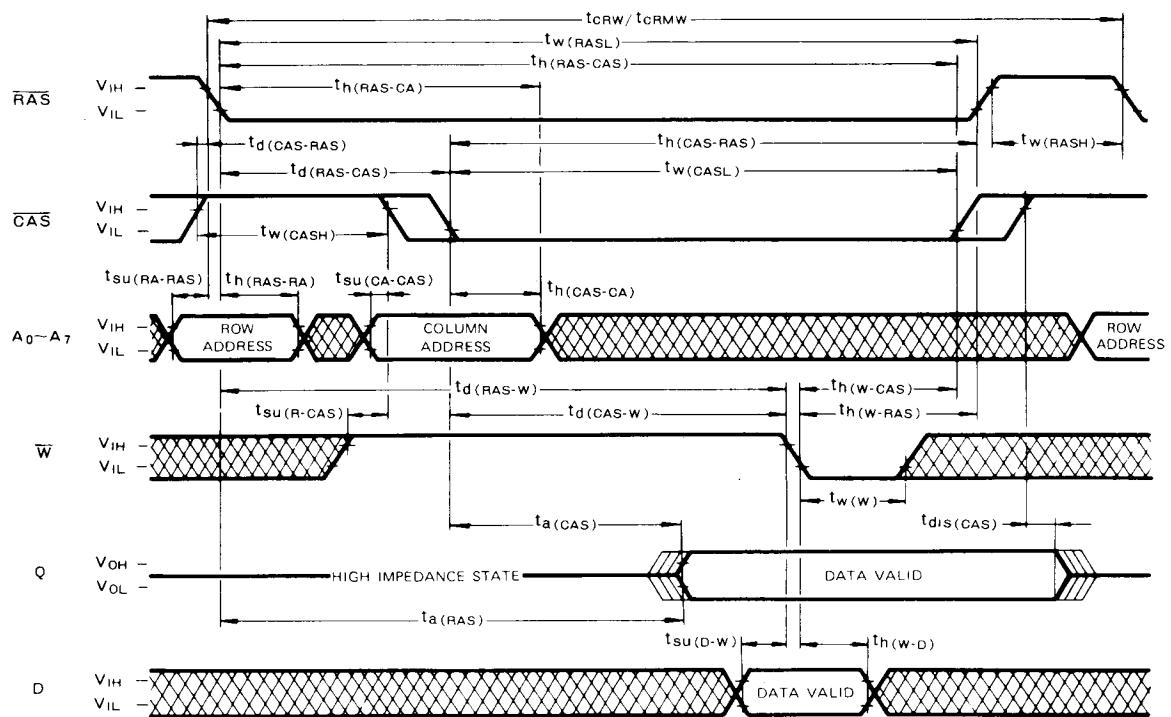


Write Cycle (Early Write)

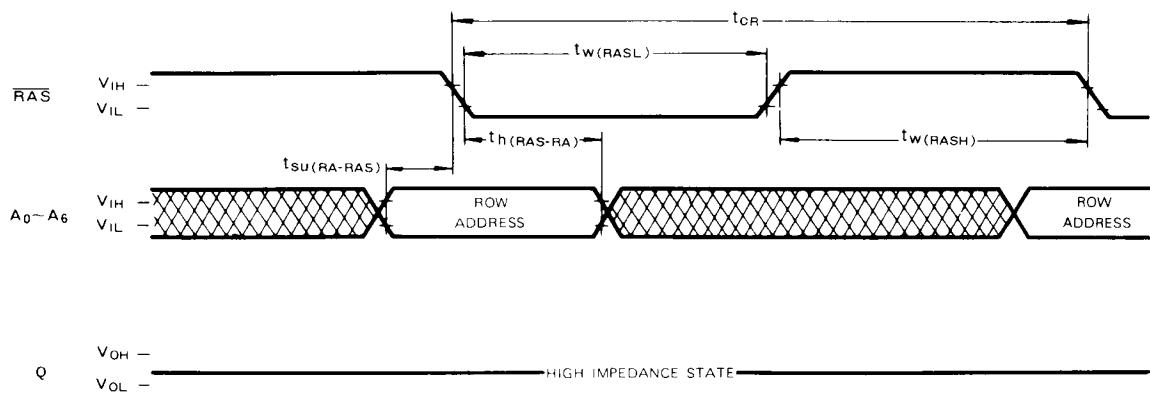


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Read-Write and Read-Modify-Write Cycles



RAS-Only Refresh Cycle (Note 19)



Note 18



Indicates the don't care input

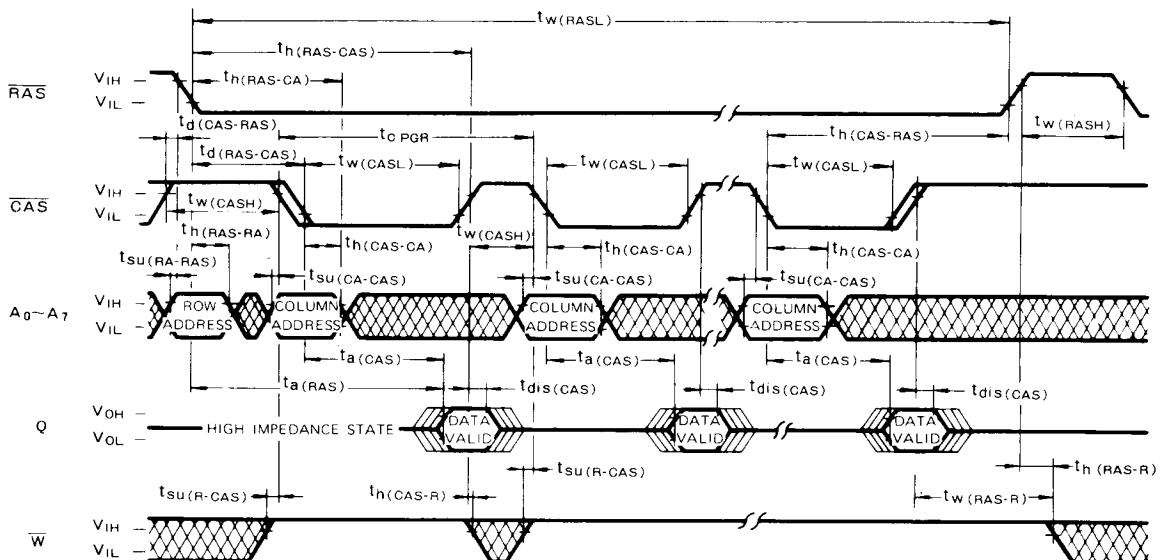


The center-line indicates the high-impedance state

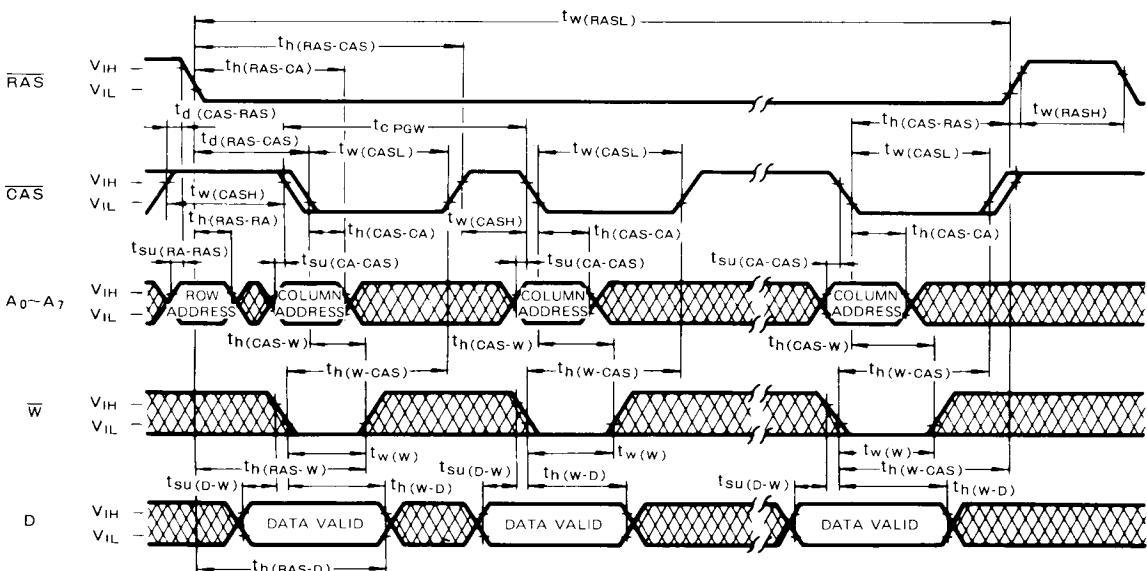
Note 19. $\overline{CAS} = V_{IH}$, \overline{W} , A_7 , D = don't care.

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Page-Mode Read Cycle



Page-Mode Write Cycle



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Hidden Refresh Cycle

